In the Claims:

1-15. canceled.

16. (currently amended) The wafer of claim [[15]] 20, wherein said wafer has an oxygen concentration of not more than 13×10^{17} atoms/cm^3 (old ASTM).

17. (currently amended) The wafer of claim [[15]] 20, wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm^3.

18. (currently amended) The wafer of claim [[16]] 20, wherein said silicon single crystal ingot has a nitrogen concentration of $1 \times 10^{13} - 1 \times 10^{15}$ atoms/cm^3.

19. (currently amended) The wafer of claim [[15]] 20, wherein said low particle density wafer and surface portion with said crystal-originated particle density is such that removal of the part of the surface portion to produce the remaining surface portion still has the surface density of crystal-originated particles of not more than 15 counts/cm^2 when the Standard Cleaning -1 is repeated six times, and each cleaning is carried out for 10 minutes.

20. (new) A silicon single crystal wafer for a particle monitor,

wherein said wafer is prepared without a heat treatment to the wafer by slicing a silicon single crystal ingot grown by the Czochralski method by controlling a time period of passing the ingot through a temperature range from 1150°C to 1070°C to be within

20 minutes and controlling a time period of passing the ingot through a temperature range from 900°C to 800°C to be within 40 minutes,

wherein said wafer comprises a wafer body having a low density of COP's and BMD's along an entire thickness of the wafer body, and

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 15 counts/cm^2, even after repeating a Standard Cleaning -1.